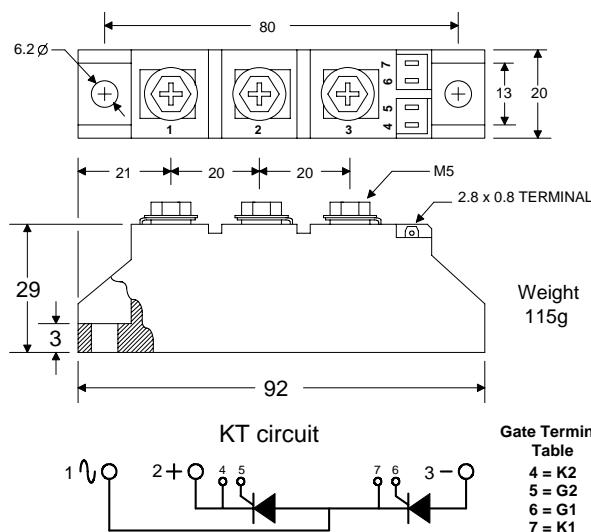


## TO-240AA compatible package



Part number scheme

**PS KT 110 N 16 STD**

1 2 3 4 5 6

- 1) Power Semiconductors initials
- 2) Circuit designation
- 3) Series number
- 4) Designates standard recovery time
- 5) Voltage Multiplier (example: 16 x 100 = 1600 Volts)
- 6) Proprietary suffix

## Features:

- ✓ All diffused silicone junctions.
- ✓ Standard recovery time for phase control applications.
- ✓ Module package compatible with JEDEC TO-240AA.
- ✓ Thick copper base plate.
- ✓ Isolated cooling, rated up to 3500 V<sub>RMS</sub>
- ✓ Easy mounting to heat sink
- ✓ Heat sink grounded.

## Voltage

| Parameter   | Symbol   | Rating   | Units   |
|---|--|--|---|
| Maximum Repetitive Off-State Voltage Notes: 1, 3, 4, 5, 6, 7  | V <sub>DRM</sub>   | 1200 ~ 1800  | Volts   |
| Maximum Repetitive Reverse Voltage Notes: 1, 3, 4, 5, 6   | V <sub>RRM</sub>   | 1200 ~ 1800  | Volts   |
| Maximum non repetitive Surge of Reverse Voltage Notes: 2, 3, 4, 5, 6                                  | V <sub>RSM</sub>   | V <sub>RRM</sub> + 100                                   | Volts   |
| Critical rate of rising off-state Voltage, Linear to 80% of V <sub>DRM</sub> Note: 2                  | dv/dt  | 500  | V/μs  |
| Note 1: T <sub>j</sub> 25°C.  | Note 2: T <sub>j</sub> 125°C.  | Note 3: Measured at the peak of the sine wave,           | Note 4: Below 0°C derate V <sub>DRM</sub> and V <sub>RRM</sub> 10%. |
| Note 5: V <sub>DRM</sub> and V <sub>RRM</sub> have I <sub>DRM</sub> , I <sub>RRM</sub> of up to 20mA. | Note 6: V <sub>DR</sub> and V <sub>RR</sub> have typical I <sub>DR</sub> , I <sub>RR</sub> of 2-3mA. | Note 7: For DC applications derate V <sub>DRM</sub> 45%. |   |
| Specifying voltage: 1400V, PSKT110N14   | 1800V, PSKT110N18  |  |   |
| 1200V, PSKT110N12   | 1600V, PSKT110N16  | Above 1800V inquire about availability.                  |   |

## Gate

| Parameter  | Symbol              | Rating                 |                 |      | Units   |
|--|---------------------|------------------------|-----------------|------|---------|
|  |                     | Temp.                  | Typ.            | Max. |         |
| Gate Trigger Voltage Note 3                                | V <sub>GT</sub>     | -20°C<br>25°C<br>125°C | 0.9<br>0.8<br>1 | 2.0  | Volts   |
| Maximum Gate Trigger Current Notes 1,3                     | I <sub>GT</sub>     | 50 ~ 120               |                 |      | mA      |
| Minimum Forward Current to Latch on-state Notes 1, 5       | I <sub>L</sub>      | 400                    |                 |      | mA      |
| Maximum permissible Gate Voltage not to Trigger Notes 1,3  | V <sub>GDM</sub>    | 250                    |                 |      | mV      |
| Maximum permissible Gate Current not to Trigger Notes 1, 3 | I <sub>GDM</sub>    | 5                      |                 |      | mA      |
| Maximum peak non repetitive Gate Voltage Notes 2, 3        | V <sub>GM</sub>     | 5                      |                 |      | Volts   |
| Maximum Negative Gate Voltage Notes 2, 4                   | -V <sub>GM</sub>    | 4                      |                 |      | Volts   |
| Maximum non repetitive Gate Current Notes 2, 3             | I <sub>GM</sub>     | 3                      |                 |      | Amperes |
| Maximum Repetitive Gate Current Notes 2, 3                 | I <sub>GRM</sub>    | 1                      |                 |      | Amperes |
| Average Gate Power (recommended) Note 2, 3                 | P <sub>G(AVE)</sub> | 50 ~ 500               |                 |      | mW      |

Note 1: T<sub>j</sub> 25°C. Note 2: T<sub>j</sub> 125°C. Note 3: Rectangular pulse, t<sub>0</sub> ≤ 8.3 ms. Note 4: Rectangular -V<sub>DC</sub> pulse, t<sub>0</sub> ≤ 8.3 ms. Note 5: Test conditions: I<sub>DC</sub> R<sub>L</sub> = 12Ω.

## Current

| Parameter  | Symbol                                    | Rating    | Units   |
|--|---|-----------|---------|
| Maximum, Average, On state, Current, Notes: 1, 2   | I <sub>T(AVE)</sub>                       | 110       | Amperes |
| Maximum, RMS, On state, Current Notes: 1, 3  | I <sub>T(RMS)</sub>                       | 175       | Amperes |
| Maximum non repetitive, Surge. On state, Current ,with no reverse voltage reapplied.   | I <sub>TSM</sub> 0%V <sub>RRM</sub>       | 2.1       | kA      |
| Maximum non repetitive, Surge, On state, Current, with maximum reverse voltage reapplied. Notes: 2, 4  | I <sub>TSM</sub> 100%V <sub>RRM</sub>     | 1.7       | kA      |
| Critical rate of rising On-state Current, non repetitive Note: 6, 7  | di/dt                                     | 150       | A/μs    |
| Holding Current Notes: 1, 5  | I <sub>H</sub>                            | 250       | mA      |
| Maximum On State Voltage drop at Maximum On State Current  | V <sub>TM</sub> @ I <sub>TM</sub>         | 1.4 @ 200 | V @ A   |
| I <sub>DRM</sub> = Maximum (threshold), Repetitive, Off-State, Current. Note: 1<br>I <sub>RRM</sub> = Maximum (threshold), Repetitive, Reverse, Current. Note: 1 | I <sub>DRM</sub> & I <sub>RRM</sub>       | 20        | mA      |
| Fuse's absolute maximum I <sup>2</sup> t with no reverse voltage   | I <sup>2</sup> t, 0% V <sub>RR</sub>      | 17.9      | kA      |
| Fuse's absolute maximum I <sup>2</sup> t with up to 100% of V <sub>RRM</sub>   | I <sup>2</sup> t, ≤ 100% V <sub>RRM</sub> | 11.6      | kA      |

Note 1: T<sub>j</sub> 55°C, Air Cooled Note 2: 120° Conduction, 60 Hz, Sinewave Note 3: 180° Conduction, 60 Hz, Sinewave

Note 4: Test conditions I<sub>DC</sub> R<sub>L</sub> = 12Ω Note 5: Switching from V<sub>DRM</sub> < 1000V

Note 6: In addition to 0.2/μF and 20Ω snubber circuit